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### **Electrical ratings** 1

Table 1.	Absolute	maximum	ratings
	ADSUIULE	maximum	raungs

Symbol	Parameter	Value	Unit
V <sub>DS</sub>	Drain-source voltage (V <sub>GS</sub> = 0)	30	V
V <sub>DGR</sub>	Drain-gate voltage ( $R_{GS} = 20 \text{ k}\Omega$ )	30	V
V <sub>GS</sub>	Gate-source voltage	± 20	V
۱ <sub>D</sub>	Drain current (continuous) at $T_C = 25^{\circ}C$	80	Α
۱ <sub>D</sub>	Drain current (continuous) at $T_C = 100^{\circ}C$	60	A
I <sub>DM</sub> <sup>(1)</sup>	Drain current (pulsed)	320	A
	Derating factor	1	
P <sub>TOT</sub>	Total dissipation at $T_C = 25^{\circ}C$	150	w
dv/dt (2)	Peak diode recovery voltage slope	7	V/ns
T <sub>J</sub> Tstg	Operating junction temperature Storage temperture	-55 to 175	°C

Table 2. Thermal resistance	•
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1. Pulse widt	n limited by safe operating area		
2. I <sub>SD</sub> <u>≤</u> 20A,	di/dt $\leq$ 100A/µs, V <sub>DD</sub> = 80% V <sub>(BP)DS</sub>		
Table 2.	Thermal resistance		
Symbol	Firimeter	Value	Unit
R <sub>thJC</sub>	Thermal esistance junction-case Max	1	°C/W
R <sub>thJA</sub>	Therrai resistance junction-ambient Max	62.5	°C/W
R	Maximum lead temperature for soldering purpose	300	°C

### Avalanche characteristics

R	Maximum lead temperature for soldering purpose	300	°C
Table 3.	Avalanche characteristics		
Symbol	Parameter	Max Value	Unit
I <sub>AR</sub>	Avalanche current, repetitive or not-repetitive (pulse width limited by Tj max)	80	A
E <sub>AS</sub>	Single pulse avalanche energy	600	mJ



### 2 **Electrical characteristics**

(T<sub>CASE</sub> = 25°C unless otherwise specified)

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
V <sub>(BR)DSS</sub>	Drain-source breakdown voltage	$I_{\rm D} = 250 \mu \text{A}, V_{\rm GS} = 0$	30			V
I <sub>DSS</sub>	Zero gate voltage drain current (V <sub>GS</sub> = 0)	$V_{DS} = Max rating,$ $V_{DS} = Max rating @125°C$			1 10	μΑ μΑ
I <sub>GSS</sub>	Gate body leakage current (V <sub>DS</sub> = 0)	$V_{DS} = \pm 20V$		. (	<u>і</u> г і ОС	nA
V <sub>GS(th)</sub>	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 250 \mu A$	1	1.7	2.5	V
R <sub>DS(on)</sub>	Static drain-source on resistance	$V_{GS} = 10 \text{ V}, I_D = 40 \text{A}$ $V_{GS} = 4.5 \text{ V}, I_D = 40 \text{A}$	27	U.005	0.006 0.008	Ω Ω
Table 5.	Dynamic	lete		.70	311	

#### Table 4. **On/off states**

#### Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
${g_{fs}}^{(1)}$	Forward transconductance	$V_{DS} > I_{D(on)} \times R_{DS(on)max},$ $v_D = 40A$	30	50		S
C <sub>iss</sub> C <sub>oss</sub> C <sub>rss</sub>	Input capacitance Output capacitance Reverse Transfor Capachance	V <sub>DS</sub> = 25V, f = 1 MHz, V <sub>GS</sub> =0		6500 1500 500		pF pF pF
Q <sub>g</sub> Q <sub>gs</sub> (∡ <sub>)d</sub>	Tc tal gate charge Gate-source charge Gate-drain charge	$V_{DD} = 24 \text{ V}, \text{ I}_{D} = 80\text{A},$ $V_{GS} = 5\text{V}$		95 30 44	130	nC nC nC

	- 155	Capacitancia	$\mathbf{O}$				
	Q <sub>g</sub> Q <sub>gs</sub> (∡ <sub>)d</sub>	Tc tal gate charge Gate-source charge Gate-drain charge	$V_{DD} = 24 \text{ V}, \text{ I}_D = 80\text{A},$ $V_{GS} = 5\text{V}$		95 30 44	130	nC nC nC
76	). Pulsed:	oulse duration = 300µs, duty cycle	9 1.5%				
0.	Table 6.	Switching times					
	Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
C	t <sub>d(on)</sub>	Turn-on delay time	V <sub>DD</sub> = 15 V, I <sub>D</sub> = 40 A		40	55	ns
;0``	t <sub>r</sub>	Rise time	$R_G = 4.7\Omega V_{GS} = 4.5 V$ Figure 12.		260	350	ns
	t <sub>r(Voff)</sub>	Off-voltage rise time	$V_{DD} = 24 \text{ V}, I_D = 80 \text{ A},$		70	95	ns
	t <sub>f</sub>	Fall time	$R_G = 4.7\Omega$ , $V_{GS} = 5V$		165	220	ns
	t <sub>c</sub>	Cross over time	Figure 12.		250	340	ns

Symbol	Parameter	Test conditions	Min	Тур.	Мах	Unit
I <sub>SD</sub> I <sub>SDM</sub> <sup>(1)</sup>	Source-drain current Source-drain current (pulsed)				80 320	A A
V <sub>SD</sub> <sup>(2)</sup>	Forward on voltage	I <sub>SD</sub> = 80A, V <sub>GS</sub> = 0			1.5	v
t <sub>rr</sub> Q <sub>rr</sub> I <sub>RRM</sub>	Reverse recovery time Reverse recovery charge Reverse recovery current	$I_{SD} = 80 \text{ A},$ di/dt = 100A/µs, V <sub>DD</sub> = 15 V, T <sub>J</sub> = 150°C <i>Figure 15.</i>		75 0.14 4		ns nC A
	h limited by safe operating area bulse duration = 300µs, duty cycle 1.5	1	1	6	19	
			2	JC		
		P	0	<u>ر</u>	19	2
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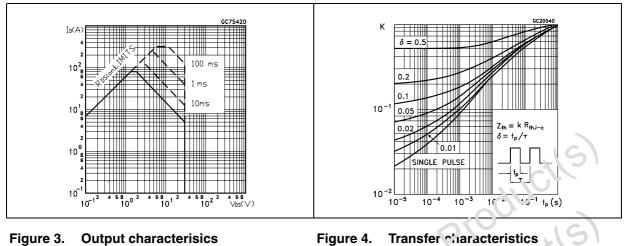
Table 7. Source drain diode

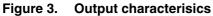


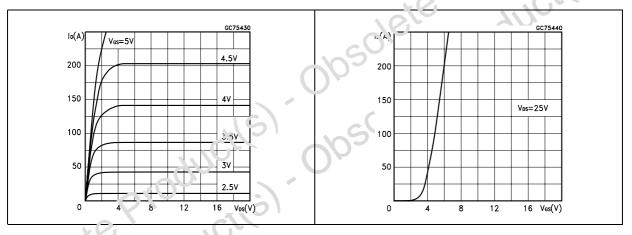
#### **Electrical characteristics (curves)** 2.1

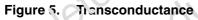
#### Figure 1. Safe operating area

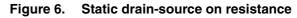
Figure 2. Thermal impedance



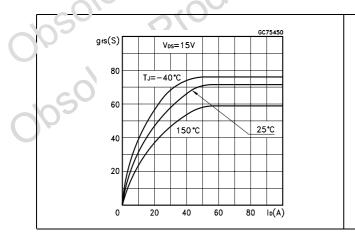


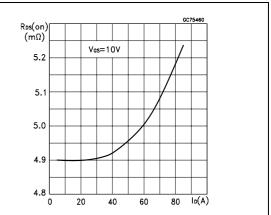




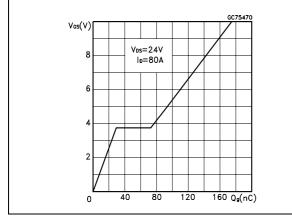


Transfer characteristics





### Figure 7. Gate charge vs gate-source voltage Figure 8. Capacitance variations



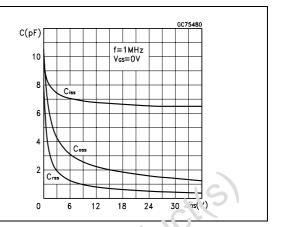


Figure 9. Normalized gate threshold voltage vs temperature

Figure 10. Normalized on resistance vs temperature

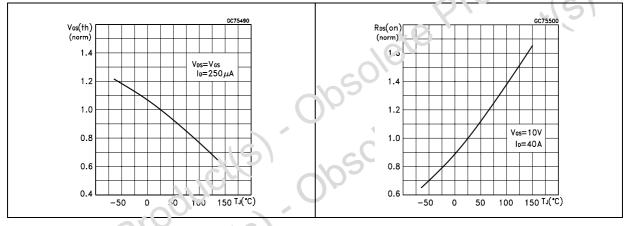
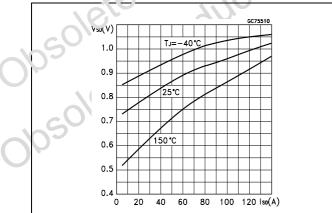
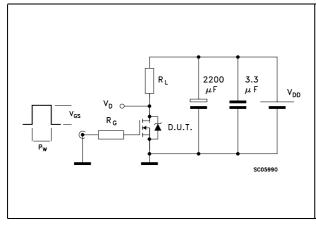


Figure 11. Source-drain diode forward cheracteristics



# 3 Test circuit

Figure 12. Switching times test circuit for resistive load



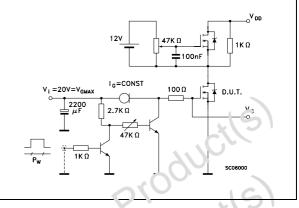
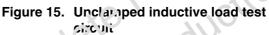
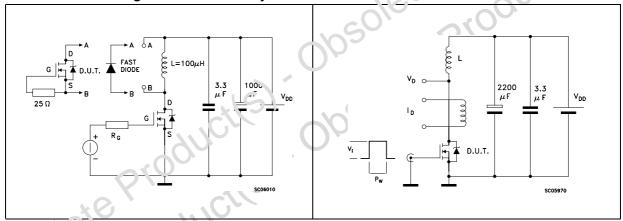
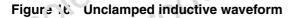


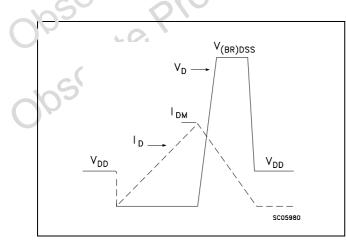
Figure 13. Gate charge test circuit

Figure 14. Test circuit for inductive load switching and diode recovery times











## 4 Package mechanical data

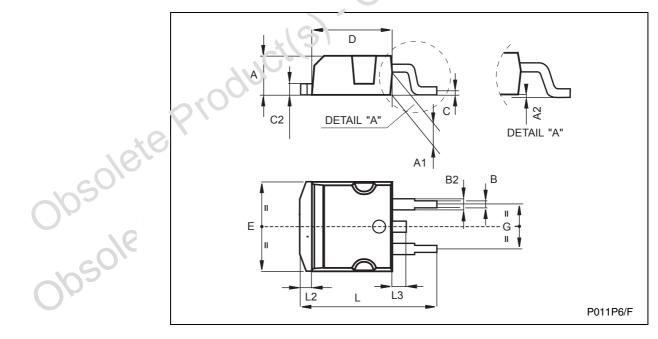
In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

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DIM.		mm			inch	
2	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
А	4.4		4.6	0.173		0.181
A1	2.49		2.69	0.098		0.106
В	0.7		0.93	0.027		0.036
B2	1.14		1.7	0.044		J.L97
С	0.45		0.6	0.017	11	0.023
C2	1.23		1.36	0.048	0	0.053
D	8.95		9.35	0.352	70	0.368
Е	10		10.4	0 293		0.409
G	4.88		5.28	0.132		0.208
L	15		15.85	0.590		0.624
L2	1.27		1.4	0.050		0.055
L3	1.4		1.75	0.055		0.068

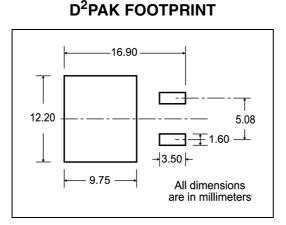
## TO-263 (D<sup>2</sup>PAK) MECHANICAL DATA



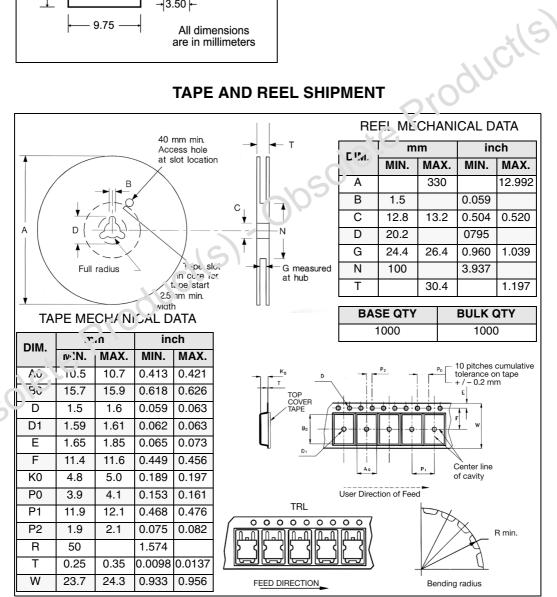
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## Packaging mechanical data



## **TAPE AND REEL SHIPMENT**



on sales type

## 6 Revision history

### Table 8. Revision history

Date	Revision	Changes
21-Jun-2004	5	Preliminary version
25-Jul-2006	6	New template, SOA updated

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